



Docket No.: M4065.0051/P051-A  
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:  
Leonard Forbes, et al.

Application No.: 09/609,813

Filed: July 3, 2000

For: HIGH DENSITY PLANAR SRAM CELL  
USING BIPOLAR LATCHUP AND GATED  
DIODE BREAKDOWN

Group Art Unit: 2815

Examiner: P. Brock, II

TECHNOLOGY CENTER 2800

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FIRST PRELIMINARY AMENDMENT

Box Non-Fee Amendment  
Commissioner for Patents  
Washington, DC 20231

Dear Sir:

Prior to examination on the merits, please amend the above-identified U.S.  
patent application as follows:

In the Claims:

Please rewrite claims 48 and 55 as follows:

48. (Thrice Amended) A method of forming a circuit for storing information as  
one of at least two possible stable current states, the method comprising the following  
steps:

providing a semiconductor substrate;

providing doped silicon regions to form a multi-region planar thyristor having at  
least four regions;